

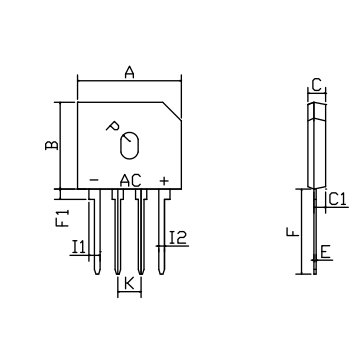
Silicon Bridge Rectifiers

GBU8A--GBU8M

FEATURES

- Rating to 1000V PRV
- Surge overload rating to 200 Amperes peak
- Ideal for printed circuit board
- Reliable low cost construction utilizing molded plastic technique results in inexpensive product
- Lead solderable per MIL-STD-202 method 208
- Glass passivated junctions

PACKAGE OUTLINE DIMENSIONS



GBU 4-SIP		
Dim	Min	Max
A	22.00	22.40
B	18.40	18.80
C	3.40	3.95
C1	2.50	3.00
E	0.40	0.60
F	17.00min	
F1	1.70	2.30
I1	2.30	2.60
I2	0.95	1.25
K	4.70	5.30
P	R1.9typical	
All Dimensions in mm		

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

		GBU 8A	GBU 8B	GBU 8D	GBU 8G	GBU 8J	GBU 8K	GBU 8M	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forward Output current @ $T_C=100^\circ C$	$I_{F(AV)}$	8.0							A
Peak forward surge current 8.3ms single half-sine-wav superimposed on rated load	I_{FSM}	200							A
Maximum instantaneous forward voltage @4.0A	V_F	1.0							V
Maximum reverse current @ $T_A=25^\circ C$ at rated DC blocking voltage @ $T_A=125^\circ C$	I_R	5.0 0.5							μA mA
Operating junction temperature range	T_J	- 55 ---- + 150							$^\circ C$
Storage temperature range	T_{STG}	- 55 ---- + 150							$^\circ C$

PACKAGE INFORMATION

Device	Package	Shipping
GBU8A--GBU8M	GBU 4-SIP	500 Units/Box

Silicon Bridge Rectifiers

GBU8A--GBU8M

FIG.1 – TYPICAL FORWARD CURRENT DERATING CURVE

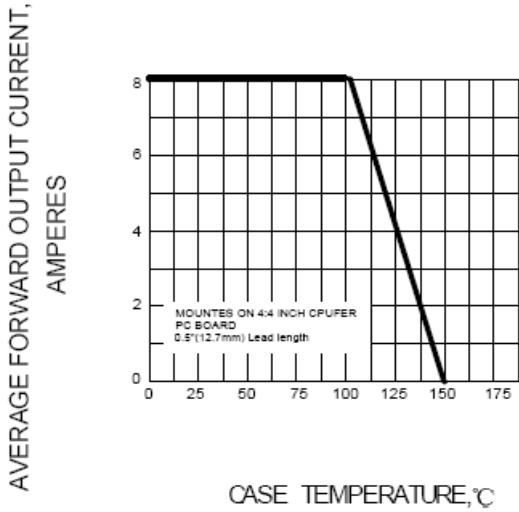


FIG.2 – MAXIMUM FORWARD SURGE CURRENT

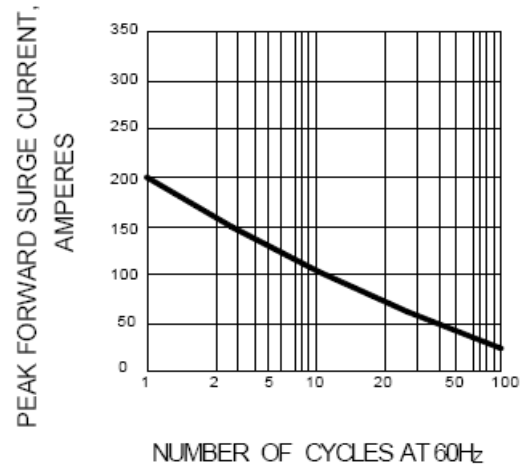


FIG.3 – TYPICAL FORWARD CHARACTERISTIC

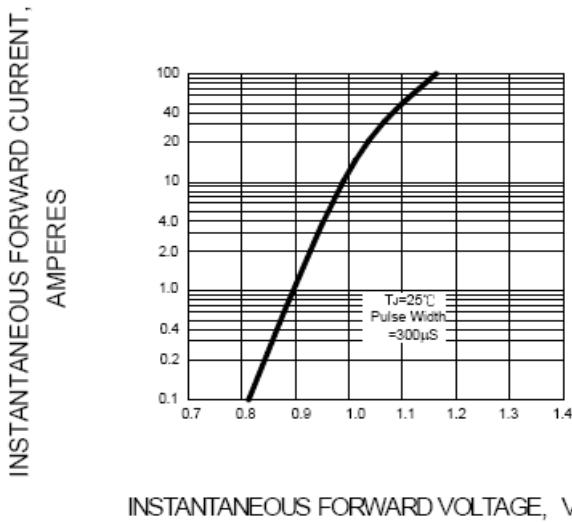


FIG.4 – TYPICAL REVERSE CHARACTERISTIC

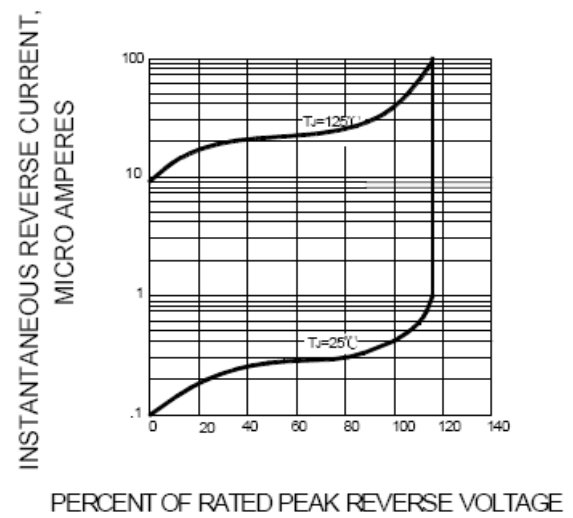


FIG.5 – TYPICAL JUNCTION CAPACITANCE PER ELEMENT

